documentation

# OPA838 1-mA, 300-MHz Gain Bandwidth, Voltage-Feedback Op Amp 

## 1 Features

- Gain bandwidth product: 300 MHz
- Very-low (trimmed) supply current: $950 \mu \mathrm{~A}$
- Bandwidth: $90 \mathrm{MHz}\left(\mathrm{A}_{\mathrm{V}}=6 \mathrm{~V} / \mathrm{V}\right)$
- High full-power bandwidth: $45 \mathrm{MHz}, 4 \mathrm{~V}_{\mathrm{PP}}$
- Negative rail input, rail-to-rail output
- Single-supply operating range: 2.7 V to 5.4 V
- $25^{\circ} \mathrm{C}$ input offset: $\pm 125 \mu \mathrm{~V}$ (maximum)
- Input offset voltage drift: $< \pm 1.6 \mu \mathrm{~V} /{ }^{\circ} \mathrm{C}$ (maximum)
- Input voltage noise: $1.8 \mathrm{nV} / \mathrm{JHz}(>200 \mathrm{~Hz})$
- Input current noise: $1 \mathrm{pA} / \mathrm{NHz}$ (> 2000 Hz )
- < $1-\mu \mathrm{A}$ shutdown current for power savings


## 2 Applications

- Low-power transimpedance amplifier
- Low-noise high-gain stage
- 12-bit to 16 -bit low-power SAR ADC driver
- High-gain active filter design
- Ultrasonic flow meter


## 3 Description

The OPA838 decompensated voltage-feedback operational amplifier provides a high $300-\mathrm{MHz}$ gain bandwidth product with $1.8-\mathrm{nV} / \mathrm{JHz}$ input noise voltage, requiring only a trimmed $0.95-\mathrm{mA}$ supply current. These features combine to provide an extremely power-efficient device for photodiode transimpedance designs and high-voltage gain stages, which require the lowest input voltage noise in signal receiver applications.
Operating at the minimum recommended noninverting gain of $6 \mathrm{~V} / \mathrm{V}$ results in a $90-\mathrm{MHz},-3-\mathrm{dB}$ bandwidth. Extremely low input noise and offset voltage make the OPA838 an excellent choice for high gains. Even at a dc-coupled gain of $1000 \mathrm{~V} / \mathrm{V}$, a $300-\mathrm{kHz}$ signal bandwidth is available with a maximum output offset voltage of $\pm 125 \mathrm{mV}$.

The single-channel OPA838 is available in 6-pin SOT-23 and SC70 packages with a power shutdown feature and a 5-pin SC70 package.

Package Information

| PART NUMBER | PACKAGE $^{(1)}$ | PACKAGE SIZE ${ }^{(2)}$ |
| :---: | :--- | :--- |
| OPA838 | DBV $($ SOT-23, 6$)$ | $2.9 \mathrm{~mm} \times 2.8 \mathrm{~mm}$ |
|  | DCK $($ SC70, 5$)$ | $2 \mathrm{~mm} \times 1.25 \mathrm{~mm}$ |
|  | DCK $(\mathrm{SC} 70,6)$ | $2 \mathrm{~mm} \times 1.5 \mathrm{~mm}$ |

(1) For all available packages, see the package option addendum at the end of the data sheet.
(2) The package size (length $\times$ width) is a nominal value and includes pins, where applicable.


Single 3-V Supply, < 3-mW Photodiode Amplifier With < 1.1-pA/ $\sqrt{ } \mathrm{Hz}$ Total Input-Referred Current Noise and 100-k $\Omega$ Gain With Overall 1-MHz SSBW

## Table of Contents

1 Features. ..... 1
2 Applications ..... 1
3 Description ..... 1
4 Revision History ..... 2
5 Device Comparison Table ..... 3
6 Pin Configuration and Functions ..... 3
7 Specifications ..... 4
7.1 Absolute Maximum Ratings. ..... 4
7.2 ESD Ratings ..... 4
7.3 Recommended Operating Conditions .....  .4
7.4 Thermal Information ..... 4
7.5 Electrical Characteristics: $\mathrm{V}_{\mathrm{S}}=5 \mathrm{~V}$ ..... 5
7.6 Electrical Characteristics: $\mathrm{V}_{\mathrm{S}}=3 \mathrm{~V}$ ..... 7
7.7 Typical Characteristics: $\mathrm{V}_{\mathrm{S}}=5 \mathrm{~V}$. ..... 9
7.8 Typical Characteristics: $\mathrm{V}_{\mathrm{S}}=3 \mathrm{~V}$ ..... 12
7.9 Typical Characteristics: Over Supply Range ..... 15
8 Detailed Description. ..... 19
8.1 Overview. ..... 19
8.2 Functional Block Diagram ..... 19
8.3 Feature Description ..... 20
8.4 Device Functional Modes. ..... 23
9 Application and Implementation. ..... 27
9.1 Application Information ..... 27
9.2 Typical Applications ..... 31
9.3 Power Supply Recommendations ..... 35
9.4 Layout ..... 36
10 Device and Documentation Support ..... 37
10.1 Device Support ..... 37
10.2 Documentation Support. ..... 37
10.3 Receiving Notification of Documentation Updates. ..... 37
10.4 Support Resources ..... 37
10.5 Trademarks ..... 37
10.6 Electrostatic Discharge Caution. ..... 38
10.7 Glossary ..... 38

## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.
Changes from Revision B (October 2018) to Revision C (October 2023) ..... Page

- Updated the numbering format for tables, figures, and cross-references throughout the document ..... 1
- Changed Device Information table to Package Information, updated columns, and added note 2 .....  1
- Updated quiescent operating current values in both Electrical Characteristics tables ..... 5
Changes from Revision A (February 2018) to Revision B (October 2018) ..... Page
- Changed < $5-\mu A$ Shutdown Current to $<1-\mu A$ Shutdown Current in Features section ..... 1
- Changed value of common-mode and differential-mode input impedance in Electrical Characteristics: $V_{S}=5$ $V$ and Electrical Characteristics: $V_{S}=3 V$ tables .....  5
- Changed value of power-down quiescent current in Electrical Characteristics: $V_{S}=5 \mathrm{~V}$ and Electrical Characteristics: $V_{S}=3 V$ tables .....  5
- Changed $5 \mu A$ to $1 \mu A$ in Overview section ..... 19
- Changed standby current from $5 \mu A$ to $1 \mu A$ in Power-Down Operation section ..... 20
- Changed common-mode input capacitance from 1.3 pF to 1 pF in Trade-Offs in Selecting The FeedbackResistor Value section.21
- Changed $1+6.3 / 1.2=6.25 \mathrm{~V} / \mathrm{V}$, adding the $1.3-\mathrm{pF}$ device common-mode capacitance to $1+6 / 1.2=6 \mathrm{~V} / \mathrm{V}$,adding the 1-pF device common-mode capacitance in Trade-Offs in Selecting The Feedback Resistor Valuesection.21
- Changed $2 \mu A$ to $0.1 \mu A$ and $5 \mu A$ to $1 \mu A$ in last sentence of Power Shutdown Operation section. ..... 26
- Changed Power Supply Recommendations and Thermal Notes title to Power Supply Recommendations ..... 35


## 5 Device Comparison Table

| PART NUMBER ${ }^{(1)}$ | GBP (MHz) | $\mathbf{5 - V} \mathbf{I}_{\mathbf{Q}}$ <br> $(\mathbf{m A}, \mathbf{M A X I M U M}$ <br> $\mathbf{2 5} \mathbf{5}^{\circ} \mathbf{C}$ | INPUT NOISE <br> VOLTAGE <br> $(\mathbf{n V} / \sqrt{\mathbf{H z})}$ | $\mathbf{2 - \mathbf { V } _ { \mathbf { P P } \text { THD } }} \mathbf{( \mathbf { d B c } , \mathbf { 1 0 0 } \mathbf { k H z } )}$RAIL-TO-RAIL <br> INPUT/OUTPUT | DUALS |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OPA838 | 300 | 0.99 | 1.9 | -110 | Negative in/out | None |
| OPA837 | 50 | 0.625 | 4.7 | -120 | Negative in/out | OPA2837 |
| OPA835 | 30 | 0.35 | 9.3 | -100 | Negative in/out | OPA2835 |
| OPA836 | 110 | 1 | 4.8 | -115 | Negative in/out | OPA2836 |
| LMP7717 | 88 | 1.4 | 5.8 | - | Negative in/out | LMP7718 |
| OPA830 | 100 | 4.7 | 9.5 | -105 | Negative in/out | OPA2830 |
| THS4281 | 38 | 0.93 | 12.5 | 12.5 | In/out | None |

(1) For a complete selection of TI high-speed amplifiers, visit www.ti.com

## 6 Pin Configuration and Functions



Figure 6-1. DBV Package. 6-Pin SOT-23 and DCK Package, 6-Pin SC70 (Top View)


Figure 6-2. DCK Package, 5-Pin SC70 (Top View)

Pin Functions

| PIN |  |  | TYPE | DESCRIPTION |
| :---: | :---: | :---: | :---: | :---: |
| NAME | $\begin{array}{\|l\|l} \text { DBV (SOT-23), } \\ \text { DCK (SC70, 6) } \end{array}$ | DCK (SC70, 5) |  |  |
| $\overline{P D}$ | 5 | - | Input/ Output | Amplifier power down. <br> Low = disabled, high = normal operation (pin must be driven). |
| VIN- | 4 | 4 | Input/ Output | Inverting input pin |
| VIN+ | 3 | 3 | Input/ Output | Noninverting input pin |
| VOUT | 1 | 1 | Input/ Output | Output pin |
| VS- | 2 | 2 | Power | Negative power-supply pin |
| VS+ | 6 | 5 | Power | Positive power-supply input |

OPA838

## 7 Specifications

### 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ${ }^{(1)}$

|  |  | MIN | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{S}-}$ to $\mathrm{V}_{\mathrm{S}^{+}}$ | Supply voltage |  | 5.5 | V |
|  | Supply turn-on, -off maximum dV/dT( ${ }^{(2)}$ |  | 1 | V/ $/ \mathrm{s}$ |
| $\mathrm{V}_{1}$ | Input voltage | $\mathrm{V}_{\text {S- }}-0.5$ | $\mathrm{V}_{\mathrm{S}^{+}}+0.5$ | V |
| $\mathrm{V}_{1 \mathrm{I}}$ | Differential input voltage |  | $\pm 1$ | V |
| 1 | Continuous input current |  | $\pm 10$ | mA |
| 10 | Continuous output current ${ }^{(3)}$ |  | $\pm 20$ | mA |
|  | Continuous power dissipation | See Section 7.4 |  |  |
| $\mathrm{T}_{\mathrm{J}}$ | Maximum junction temperature |  | 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {A }}$ | Operating free-air temperature | -40 | 125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ | Storage temperature | -65 | 150 | ${ }^{\circ} \mathrm{C}$ |

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) Stay below this $\pm$ supply turn-on edge rate to prevent the edge-triggered ESD absorption device across the supply pins from turning on.
(3) Long-term continuous output current for electromigration limits.

### 7.2 ESD Ratings

|  |  |  | VALUE | UNIT |
| :---: | :---: | :---: | :---: | :---: |
|  |  | Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ${ }^{(1)}$ | $\pm 1500$ |  |
| $V_{\text {(ESD) }}$ | E | Charged-device model (CDM), per JEDEC specification JESD22-C101 ${ }^{(2)}$ | $\pm 1000$ |  |

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

|  |  | MIN | NOM | MAX |
| :--- | :--- | ---: | ---: | :---: |
| $V_{\text {S+ }}$ | Single-supply voltage | 2.7 | 5 | 5.4 |
| $T_{A}$ | Ambient temperature | -40 | 25 | 125 |

### 7.4 Thermal Information

| THERMAL METRIC ${ }^{(1)}$ |  | OPA838 |  |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | $\begin{gathered} \text { DBV } \\ \text { (SOT-23) } \end{gathered}$ | $\begin{gathered} \text { DCK } \\ \text { (SC70) } \end{gathered}$ | $\begin{aligned} & \text { DCKS } \\ & \text { (SC70) } \end{aligned}$ |  |
|  |  | 6 PINS | 5 PINS | 6 PINS |  |
| $\mathrm{R}_{\text {өJA }}$ | Junction-to-ambient thermal resistance | 194 | 203 | 189 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{R}_{\text {өJCtop }}$ | Junction-to-case (top) thermal resistance | 129 | 152 | 150 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{R}_{\text {өJB }}$ | Junction-to-board thermal resistance | 39 | 76 | 79 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\psi_{\text {JT }}$ | Junction-to-top characterization parameter | 26 | 58 | 61 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\Psi_{\text {JB }}$ | Junction-to-board characterization parameter | 39 | 76 | 79 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

### 7.5 Electrical Characteristics: $\mathrm{V}_{\mathrm{S}}=5 \mathrm{~V}$

at $\mathrm{V}_{\mathrm{S}_{+}}=5 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}_{-}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{F}}=1 \mathrm{k} \Omega, \mathrm{R}_{\mathrm{G}}=200 \Omega, \mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega, \mathrm{G}=6 \mathrm{~V} / \mathrm{V}$, input and output referenced to midsupply, and $\mathrm{T}_{\mathrm{A}} \approx$ $25^{\circ} \mathrm{C}$, (unless otherwise noted)


OPA838

### 7.5 Electrical Characteristics: $\mathrm{V}_{\mathrm{S}}=5 \mathrm{~V}$ (continued)

at $\mathrm{V}_{\mathrm{S}_{+}}=5 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}_{-}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{F}}=1 \mathrm{k} \Omega, \mathrm{R}_{\mathrm{G}}=200 \Omega, \mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega, \mathrm{G}=6 \mathrm{~V} / \mathrm{V}$, input and output referenced to midsupply, and $\mathrm{T}_{\mathrm{A}} \approx$ $25^{\circ} \mathrm{C}$, (unless otherwise noted)

(1) Test levels (all values set by characterization and simulation): (A) $100 \%$ tested at $25^{\circ} \mathrm{C}$, overtemperature limits by characterization and simulation; (B) Not tested in production, limits set by characterization and simulation; (C) Typical value only for information.
(2) This slew rate is the average of the rising and falling time estimated from the large-signal bandwidth as: $\left(0.8 \times V_{\text {PEAK }} / \sqrt{2}\right) \times 2 \pi \times f_{-3 d B}$ where this $\mathrm{f}_{-3 \mathrm{~dB}}$ is the typical measured $4-\mathrm{V}_{\mathrm{PP}}$ bandwidth at gains of $6 \mathrm{~V} / \mathrm{V}$.
(3) Current is considered positive out of the pin.
(4) Input offset voltage drift, input bias current drift, and input offset current drift typical specifications are mean $\pm 1 \sigma$ characterized by the full temperature range end-point data. Maximum drift specifications are set by the min, max packaged test range on the wafer-level screened drift. Drift is not specified by the final automated test equipment (ATE) or by QA sample testing.
(5) Input offset voltage drift, input bias current drift, and input offset current drift are average values calculated by taking data at the end points, computing the difference, and dividing by the temperature range.
(6) The typical specification is at $25^{\circ} \mathrm{C} \mathrm{T}_{\mathrm{J}}$. The minimum and maximum limits are expanded for the ATE to account for an ambient range from $22^{\circ} \mathrm{C}$ to $32^{\circ} \mathrm{C}$ with a $4-\mu \mathrm{A} /{ }^{\circ} \mathrm{C}$ temperature coefficient on the supply current.

### 7.6 Electrical Characteristics: $\mathrm{V}_{\mathrm{S}}=\mathbf{3} \mathrm{V}$

at $\mathrm{V}_{\mathrm{S}_{+}}=3 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}_{-}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{F}}=1 \mathrm{k} \Omega, \mathrm{R}_{\mathrm{G}}=200 \Omega, \mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega, \mathrm{G}=6 \mathrm{~V} / \mathrm{V}$, input and output referenced to midsupply, and $\mathrm{T}_{\mathrm{A}} \approx$ $25^{\circ} \mathrm{C}$, (unless otherwise noted)


OPA838

### 7.6 Electrical Characteristics: $\mathrm{V}_{\mathbf{S}}=3 \mathrm{~V}$ (continued)

at $\mathrm{V}_{\mathrm{S}_{+}}=3 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}_{-}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{F}}=1 \mathrm{k} \Omega, \mathrm{R}_{\mathrm{G}}=200 \Omega, \mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega, \mathrm{G}=6 \mathrm{~V} / \mathrm{V}$, input and output referenced to midsupply, and $\mathrm{T}_{\mathrm{A}} \approx$ $25^{\circ} \mathrm{C}$, (unless otherwise noted)

(1) Test levels (all values set by characterization and simulation): (A) $100 \%$ tested at $25^{\circ} \mathrm{C}$, overtemperature limits by characterization and simulation; (B) Not tested in production, limits set by characterization and simulation; (C) Typical value only for information.
(2) This slew rate is the average of the rising and falling time estimated from the large-signal bandwidth as: $\left(0.8 \times V_{\text {PEAK }} / \sqrt{2}\right) \times 2 \pi \times f_{-3 d B}$ where this $\mathrm{f}_{-3 \mathrm{~dB}}$ is the typical measured $2-\mathrm{V}_{\mathrm{PP}}$ bandwidth at gains of $6 \mathrm{~V} / \mathrm{V}$.
(3) Current is considered positive out of the pin.
(4) Input offset voltage drift, input bias current drift, and input offset current drift typical specifications are mean $\pm 1 \sigma$ characterized by the full temperature range end-point data. Maximum drift specifications are set by the min, max packaged test range on the wafer-level screened drift. Drift is not specified by the final automated test equipment (ATE) or by QA sample testing.
(5) Input offset voltage drift, input bias current drift, and input offset current drift are average values calculated by taking data at the end points, computing the difference, and dividing by the temperature range.
(6) The typical specification is at $25^{\circ} \mathrm{C} \mathrm{T}_{\mathrm{J}}$. The minimum and maximum limits are expanded for the ATE to account for an ambient range from $22^{\circ} \mathrm{C}$ to $32^{\circ} \mathrm{C}$ with a $4-\mu \mathrm{A} /{ }^{\circ} \mathrm{C}$ temperature coefficient on the supply current.

### 7.7 Typical Characteristics: $\mathrm{V}_{\mathbf{S}}=5 \mathrm{~V}$

at $\mathrm{V}_{\mathrm{S}_{+}}=5 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}_{-}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{F}}=1 \mathrm{k} \Omega, \mathrm{R}_{\mathrm{G}}=200 \Omega, \mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega, \mathrm{G}=6 \mathrm{~V} / \mathrm{V}$, input and output referenced to midsupply, and $\mathrm{T}_{\mathrm{A}} \approx$ $25^{\circ} \mathrm{C}$ (unless otherwise noted)


See Figure 9-1 and Table 9-1 ( $\left.\mathrm{V}_{\mathrm{O}}=20 \mathrm{mV} \mathrm{PP}, \mathrm{R}_{\text {LOAD }}=2 \mathrm{k} \Omega\right)$
Figure 7-1. Noninverting Small-Signal Frequency Response vs Gain


Figure 7-3. Noninverting Large-Signal Bandwidth vs $\mathrm{V}_{\text {OPP }}$


See Figure 9-1 and Table 9-1 ( $\mathrm{V}_{\mathrm{O}}=200 \mathrm{mV}$ PP, $\mathrm{R}_{\text {LOAD }}=2 \mathrm{k} \Omega$ )
Figure 7-5. Noninverting Response Flatness vs Gain


See Figure 9-2 and Table 9-2 ( $\left.\mathrm{V}_{\mathrm{O}}=20 \mathrm{~m} \mathrm{~V}_{\mathrm{PP}}, \mathrm{R}_{\text {LOAD }}=2 \mathrm{k} \Omega\right)$
Figure 7-2. Inverting Small-Signal Frequency Response vs Gain


Figure 7-4. Inverting Large-Signal Bandwidth vs $V_{\text {OPP }}$


See Figure 9-2 and Table 9-2 $\left(\mathrm{V}_{\mathrm{O}}=200 \mathrm{~m} \mathrm{~V}_{\mathrm{PP}} ; \mathrm{R}_{\text {LOAD }}=2 \mathrm{k} \Omega\right)$
Figure 7-6. Inverting Response Flatness vs Gain

### 7.7 Typical Characteristics: $\mathrm{V}_{\mathrm{S}}=5 \mathrm{~V}$ (continued)

at $\mathrm{V}_{\mathrm{S}_{+}}=5 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}_{-}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{F}}=1 \mathrm{k} \Omega, \mathrm{R}_{\mathrm{G}}=200 \Omega, \mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega, \mathrm{G}=6 \mathrm{~V} / \mathrm{V}$, input and output referenced to midsupply, and $\mathrm{T}_{\mathrm{A}} \approx$ $25^{\circ} \mathrm{C}$ (unless otherwise noted)


Figure 7-7. Noninverting Step Response vs $V_{\text {OPP }}$


Figure 7-9. Simulated Noninverting Settling Time


See Figure 9-1 and Table 9-1
Figure 7-11. Noninverting Overdrive Recovery


Figure 7-8. Inverting Step Response vs $\mathrm{V}_{\text {OPP }}$


Figure 7-10. Simulated Inverting Settling Time


See Figure 9-2 and Table 9-2
Figure 7-12. Inverting Overdrive Recovery

### 7.7 Typical Characteristics: $\mathrm{V}_{\mathbf{S}}=5 \mathrm{~V}$ (continued)

at $\mathrm{V}_{\mathrm{S}_{+}}=5 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}_{-}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{F}}=1 \mathrm{k} \Omega, \mathrm{R}_{\mathrm{G}}=200 \Omega, \mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega, \mathrm{G}=6 \mathrm{~V} / \mathrm{V}$, input and output referenced to midsupply, and $\mathrm{T}_{\mathrm{A}} \approx$ $25^{\circ} \mathrm{C}$ (unless otherwise noted)


See Figure 9-1, Figure 9-2, Table 9-1, and Table 9-2

Figure 7-13. Harmonic Distortion vs Frequency


See Figure 9-1, Figure 9-2, Table 9-1, and Table 9-2

$$
\mathrm{f}=100 \mathrm{kHz}, \mathrm{R}_{\mathrm{LOAD}}=2 \mathrm{k} \Omega
$$

Figure 7-15. Harmonic Distortion vs Output Swing


See Figure 9-1 and Table 9-1

$$
\mathrm{V}_{\mathrm{O}}=2 \mathrm{~V}_{\mathrm{PP}, \mathrm{f}} \mathrm{f}=100 \mathrm{kHz}, \mathrm{R}_{\mathrm{LOAD}}=2 \mathrm{k} \Omega
$$

Figure 7-17. Noninverting Distortion vs Output Common-Mode Voltage


See Figure 9-1, Figure 9-2, Table 9-1, and Table 9-2 $\mathrm{V}_{\mathrm{O}}=2 \mathrm{~V}_{\mathrm{PP}}, \mathrm{f}=100 \mathrm{kHz}$
Figure 7-14. Harmonic Distortion vs $\mathrm{R}_{\text {LOAD }}$


See Figure 9-1, Figure 9-2, Table 9-1, and Table 9-2

$$
\mathrm{V}_{\mathrm{O}}=2 \mathrm{~V}_{\mathrm{PP}}, \mathrm{R}_{\mathrm{LOAD}}=2 \mathrm{k} \Omega, \mathrm{f}=100 \mathrm{kHz}
$$

Figure 7-16. Harmonic Distortion vs Gain


See Figure 9-2 and Table 9-2
$\mathrm{V}_{\mathrm{O}}=2 \mathrm{~V}_{\mathrm{PP}}, \mathrm{f}=100 \mathrm{kHz}, \mathrm{R}_{\mathrm{LOAD}}=2 \mathrm{k} \Omega$
Figure 7-18. Inverting Distortion vs Output Common-Mode Voltage

### 7.8 Typical Characteristics: $V_{\mathbf{S}}=3 \mathrm{~V}$

at $\mathrm{V}_{\mathrm{S}_{+}}=3 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}_{-}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{F}}=1 \mathrm{k} \Omega, \mathrm{R}_{\mathrm{G}}=200 \Omega, \mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega, \mathrm{G}=6 \mathrm{~V} / \mathrm{V}$, input and output referenced to midsupply, and $\mathrm{T}_{\mathrm{A}}=$ $25^{\circ} \mathrm{C}$ (unless otherwise noted)


See Figure 9-1 and Table 9-1
Figure 7-19. Noninverting Small-Signal Response vs Gain


Figure 7-21. Noninverting Large-Signal Bandwidth vs $\mathrm{V}_{\text {OPP }}$


See Figure 9-1 and Table 9-1 ( $\mathrm{V}_{\mathrm{O}}=200 \mathrm{~m} \mathrm{~V}_{\mathrm{PP}}, \mathrm{R}_{\text {LOAD }}=2 \mathrm{k} \Omega$ )
Figure 7-23. Noninverting Response Flatness vs Gain


See Figure 9-2 and Table 9-2
Figure 7-20. Inverting Small-Signal Response vs Gain


See Figure 9-2 ( $\left.A_{V}=-6 \mathrm{~V} / \mathrm{V}\right)$
Figure 7-22. Inverting Large-Signal Bandwidth vs $\mathrm{V}_{\text {OPP }}$


See Figure 9-2 and Table 9-2 $\left(\mathrm{V}_{\mathrm{O}}=200 \mathrm{~m} \mathrm{~V}_{\mathrm{PP}}, \mathrm{R}_{\text {LOAD }}=2 \mathrm{k} \Omega\right)$
Figure 7-24. Inverting Response Flatness vs Gain

### 7.8 Typical Characteristics: $\mathrm{V}_{\mathbf{S}}=3 \mathrm{~V}$ (continued)

at $\mathrm{V}_{\mathrm{S}_{+}}=3 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}_{-}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{F}}=1 \mathrm{k} \Omega, \mathrm{R}_{\mathrm{G}}=200 \Omega, \mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega, \mathrm{G}=6 \mathrm{~V} / \mathrm{V}$, input and output referenced to midsupply, and $\mathrm{T}_{\mathrm{A}}=$ $25^{\circ} \mathrm{C}$ (unless otherwise noted)


### 7.8 Typical Characteristics: $\mathrm{V}_{\mathbf{S}}=3 \mathrm{~V}$ (continued)

at $\mathrm{V}_{\mathrm{S}_{+}}=3 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}_{-}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{F}}=1 \mathrm{k} \Omega, \mathrm{R}_{\mathrm{G}}=200 \Omega, \mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega, \mathrm{G}=6 \mathrm{~V} / \mathrm{V}$, input and output referenced to midsupply, and $\mathrm{T}_{\mathrm{A}}=$ $25^{\circ} \mathrm{C}$ (unless otherwise noted)


See Figure 9-1, Figure 9-2, Table 9-1, and Table 9-2
Figure 7-31. Harmonic Distortion vs Frequency


See Figure 9-1, Figure 9-2, Table 9-1, and Table 9-2

Figure 7-33. Harmonic Distortion vs Output Swing


See Figure 9-1 and Table 9-1, $\mathrm{V}_{\mathrm{O}}=1 \mathrm{~V}$ PP
Figure 7-35. Noninverting Harmonic Distortion vs Output Common-Mode Voltage


See Figure 9-1, Figure 9-2, Table 9-1, and Table 9-2
Figure 7-32. Harmonic Distortion vs Load


See Figure 9-1, Figure 9-2, Table 9-1, and Table 9-2 2-k load, $2 \mathrm{~V}_{\mathrm{PP}}$
Figure 7-34. Harmonic Distortion vs Gain


See Figure 9-2 and Table 9-2, $\mathrm{V}_{\mathrm{O}}=1 \mathrm{~V}$ PP
Figure 7-36. Inverting Harmonic Distortion vs Output CommonMode Voltage

### 7.9 Typical Characteristics: Over Supply Range

at $\overline{P D}=\mathrm{V}_{\mathrm{S}+}$ and $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ (unless otherwise noted)


Figure 7-37. Open-Loop Gain and Phase


Figure 7-39. Input Spot Noise Density


Figure 7-41. PSRR and CMRR


See Figure 9-1 and Table 9-1 (simulation)
Figure 7-38. Closed-Loop Output Impedance


Figure 7-40. Low-Frequency Voltage Noise


Figure 7-42. Disabled Isolation Noninverting Input to Output

OPA838

### 7.9 Typical Characteristics: Over Supply Range (continued)

at $\overline{P D}=\mathrm{V}_{\mathrm{S}+}$ and $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ (unless otherwise noted)


Figure 7-43. Input Offset Voltage Distribution


Figure 7-45. Input Offset Voltage vs Temperature


Figure 7-47. Input Offset Voltage Drift Distribution


Figure 7-44. Input Offset Current Distribution


Figure 7-46. Input Offset Current vs Temperature


Figure 7-48. Input Offset Current Drift Distribution

### 7.9 Typical Characteristics: Over Supply Range (continued)

at $\overline{P D}=V_{S+}$ and $T_{A}=25^{\circ} \mathrm{C}$ (unless otherwise noted)


Figure 7-51. Turn-On Time to Sinusoidal Input


Single-supply, DC input to produce midscale output (simulation)
Figure 7-53. Gain of 6-V/V Turn-On Time to Final DC Value at Midscale


See Figure 8-6 and Table 9-1
2-k $\Omega$ parallel load to $C_{\text {LOAD }}$
Figure 7-50. Small-Signal Response Shapes vs C Load With Recommended Rout


Figure 7-52. Turn-Off Time to Sinusoidal Input


Single-supply, DC input to produce midscale output (simulation)
Figure 7-54. Gain of 10-V/V Turn-On Time to Final DC Value at Midscale

### 7.9 Typical Characteristics: Over Supply Range (continued)

at $\overline{P D}=V_{S+}$ and $T_{A}=25^{\circ} \mathrm{C}$ (unless otherwise noted)


Figure 7-55. Output Voltage Swing vs Load Resistor


Figure 7-57. Quiescent Current vs Temperature


5 units, $3-\mathrm{V}$ and $5-\mathrm{V}$ supplies
Figure 7-59. Input Offset Voltage vs Input CommonMode Voltage


Figure 7-56. Output Saturation Voltage vs Load Current


Figure 7-58. Supply Current vs Power-Down Voltage: Turn On Higher Than Turn Off


Figure 7-60. Input Bias and Offset Current vs $\mathbf{V}_{\text {ICM }}$

## 8 Detailed Description

### 8.1 Overview

The OPA838 is a power-efficient, decompensated, voltage-feedback amplifier (VFA). Combining a negative-rail input stage and a rail-to-rail output (RRO) stage, the device provides a flexible option where higher gain or transimpedance designs are required. This $300-\mathrm{MHz}$ gain-bandwidth product (GBP) amplifier requires less than 1 mA of supply current over a $2.7-\mathrm{V}$ to $5.4-\mathrm{V}$ total supply operating range. A shutdown feature on the 6 -pin package versions provides power savings where the system requires less than $1 \mu \mathrm{~A}$ when shut down. A decompensated amplifier operating at low gains (less than $6 \mathrm{~V} / \mathrm{V}$ ) can experience a low phase margin that risks oscillation. The TINA model for the OPA838 predicts those conditions.

### 8.2 Functional Block Diagram

The OPA838 is a standard voltage-feedback op amp with two high-impedance inputs and a low-impedance output. Standard applications circuits are supported; see Figure 8-1 and Figure 8-2. These application circuits are shown with a dc $\mathrm{V}_{\text {REF }}$ on the inputs that set the dc operating points for single-supply designs. The $\mathrm{V}_{\text {REF }}$ is often ground, especially for split-supply applications.


Figure 8-1. Noninverting Amplifier


Figure 8-2. Inverting Amplifier

OPA838

### 8.3 Feature Description

### 8.3.1 Input Common-Mode Voltage Range

When the primary design goal is a linear amplifier with high CMRR, the input pins must stay within the input operating range ( $\mathrm{V}_{\mathrm{ICR}}$ ). These input pins are referenced off of each supply as an input headroom requirement. Specified operation at $25^{\circ} \mathrm{C}$ is maintained to the negative supply voltage, and to within 1.3 V of the positive supply voltage. The common-mode input range specifications in the table data use CMRR to set the limit. The limits are selected to make sure CMRR does not degrade more than 3 dB less than the minimum CMRR value if the input voltage is within the specified range.

During linear operation, the voltage difference between the input pins is small ( 0 V ) and the input common-mode voltage is analyzed at either input pin, as both pins are at the same potential. The voltage at $\mathrm{V}_{\mathbb{I N +}}$ is simple to evaluate. In noninverting configuration (see Figure 8-1), the input signal ( $\mathrm{V}_{\text {IN }}$ ) must not violate the $\mathrm{V}_{\text {ICR }}$. In inverting configuration (see Figure 8-2), the reference voltage ( $\mathrm{V}_{\mathrm{REF}}$ ), must be within the $\mathrm{V}_{\text {ICR }}$.

The input voltage limits have fixed headroom to the power rails and track the power supply voltages. For a single $5-\mathrm{V}$ supply, the linear $25^{\circ} \mathrm{C}$ minimum input voltage ranges from 0 V to 3.7 V , and 0 V to 1.4 V for a single $2.7-\mathrm{V}$ supply. The delta headroom from each power supply rail is the same in each case ( 0 V and 1.3 V ).

### 8.3.2 Output Voltage Range

The OPA838 device is a rail-to-rail output op amp. Rail-to-rail output typically means that the output voltage swings to within 100 mV of the supply rails. There are different ways to specify this: one is with the output still in linear operation and another is with the output saturated. Saturated output voltages are closer to the power supply rails than linear outputs, but the signal is not a linear representation of the input. Saturation and linear operation limits are affected by the output current, where higher currents lead to more voltage loss in the output transistors; see Figure 7-56.

The specification tables show saturated output voltage specifications with a $2-\mathrm{k} \Omega$ load. Figure 7-11 and Figure 7-43 illustrate saturated voltage-swing limits versus output load resistance, and Figure 7-12 and Figure 7-44 illustrate the output saturation voltage versus load current. With a light load, the output voltage limits have constant headroom to the power rails and track the power supply voltages. For example, with a $1-\mathrm{k} \Omega$ load and a single 5-V supply, the linear output voltage ranges from 0.12 V to 4.88 V and ranges from 0.12 V to 2.58 V for a $2.7-\mathrm{V}$ supply. The delta from each power supply rail is the same in each case: 0.12 V .

With devices like the OPA838 where the input range is lower than the output range, the input limits the available signal swing at low gains. Because the OPA838 is intended for higher gains, the smaller input swing range does not limit operation and full rail-to-rail output is available. Inverting voltage gain and transimpedance configurations are typically limited by the output voltage limits of the op amp if the noninverting input pin is biased in range.

### 8.3.3 Power-Down Operation

The OPA838 includes a power-down feature. Under logic control, the amplifier can switch from normal operation to a standby current of less than $1 \mu \mathrm{~A}$. When the PD pin is connected high (greater than or equal to 1.5 V over the negative supply), the amplifier is active. Connecting the $\overline{\mathrm{PD}}$ pin low (less than or equal to 0.55 V over the negative supply) disables the amplifier. To protect the input stage of the amplifier, the device uses internal, back-to-back diodes (two in series each way) between the inverting and noninverting input pins. If the differential voltage in shutdown exceeds 1.2 V , those diodes turn on.

Actively drive the $\overline{P D}$ pin high or low; do not float this pin. If the power-down mode is not used, tie the $\overline{P D}$ pin to the positive supply rail.

When the op amp is powered from a single-supply and ground, with $\overline{P D}$ driven from logic devices with similar $V_{D D}$ voltages to the op amp, no special considerations are required. When the op amp is powered from a splitsupply with $\mathrm{V}_{\mathrm{S}}$ less than ground, an open-collector type of interface with a pullup resistor is more appropriate. Pullup resistor values must be less than $100 \mathrm{k} \Omega$. Recovery from power down is illustrated in Figure 7-53 and Figure 7-54 for several gains. In single-supply mode, with the gain resistor at ground, the output approaches the
positive supply on initial power-up until the internal nodes charge, and then recover to the target output voltage; see Figure 7-51 and Figure 7-52.

### 8.3.4 Trade-Offs in Selecting The Feedback Resistor Value

The OPA838 is specified using a $1-\mathrm{k} \Omega$ feedback resistor with a $200-\Omega$ gain resistor to ground in a noninverting gain of $6 \mathrm{~V} / \mathrm{V}$ configuration. These values give a good compromise, keeping the noise contribution of the resistors well below that of the amplifier noise terms and minimal power in the feedback network as the output voltage swing creates load current back into the feedback network. Decreasing these values improves the noise at the cost of more power dissipated in the feedback network. Low values increase the harmonic distortion as the feedback load decreases. Increasing the $R_{F}$ value at a particular gain increases the output noise contribution of those resistors possibly becoming dominant. As the feedback resistor values continue to increase (and the $R_{G}$ at a fixed target gain), there is a loss of phase margin as the impedance that drives the inverting input capacitance brings in an added loop pole at lower frequencies. Figure $8-3$ shows this at a gain of $6 \mathrm{~V} / \mathrm{V}$ with increasing $R_{F}$ values. This noninverting test shows more peaking as the $R_{F}$ values increase due to the $1-p F$ common-mode input capacitance at the inverting input. The TINA simulation model gives excellent prediction of these effects.


Figure 8-3. Frequency Response With Various Feedback Resistor Values
Operating the OPA838 in inverting mode with higher $R_{F}$ values increases response peaking due to the loss of phase margin effect. In the inverting case, a pair of capacitors can flatten the response at the cost of lower closed-loop bandwidth. Figure $8-4$ shows an example with a $20-\mathrm{k} \Omega \mathrm{R}_{\mathrm{F}}$ value at an inverting gain of $-5 \mathrm{~V} / \mathrm{V}$ (noise gain $=6 \mathrm{~V} / \mathrm{V}$ ) with optional capacitors $\left(\mathrm{C}_{\mathrm{F}}\right.$ and $\left.\mathrm{C}_{\mathrm{G}}\right)$. Figure 8-4 shows optional bias current cancellation elements on the noninverting input. The total resistance value matches the parallel combination of $R_{G} \| R_{F}$, which reduces the $D C$ output error term due to bias current to $I_{O S} \times R_{F}$. The $10-\mathrm{nF}$ capacitor is added across the larger part of this bias current canceling resistance to filter noise and the $20 \Omega$ is split out to isolate the capacitor self resonance from the noninverting input. Figure 8-5 illustrates the small-signal response shape with and without these capacitors. The feedback capacitor $\left(C_{F}\right)$, is selected to set a desired closed-loop bandwidth with $\mathrm{R}_{\mathrm{F}} . \mathrm{C}_{\mathrm{G}}$ is added to ground to shape the noise gain up over frequency to be greater than or equal to $6 \mathrm{~V} / \mathrm{V}$ at higher frequencies. In this example, that higher frequency noise gain is $1+6 / 1.2=6 \mathrm{~V} / \mathrm{V}$, adding the $1-\mathrm{pF}$ device common-mode capacitance to the external 5 pF . Using the capacitors to set the feedback ratio removes the pole produced in the feedback driving from purely resistive source to the inverting parasitic capacitance.

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Figure 8-4. G = -5 V/V With Optional Compensation


Figure 8-5. Inverting Response With and Without Compensation

### 8.3.5 Driving Capacitive Loads

The OPA838 can drive small capacitive loads directly without oscillation (less than 6@pF). When driving capacitive loads greater than 6 pF , Figure 7-49 illustrates the recommended $\mathrm{R}_{\text {OUt }}$ vs capacitor load parametric on gains. At higher gains, the amplifier starts with greater phase margin into a resistive load and can operate with lower R OUt for a given capacitive load. Without $\mathrm{R}_{\text {OUT }}$, output capacitance interacts with the output impedance of the amplifier, which causes phase shift in the loop gain of the amplifier that reduces the phase margin. This causes peaking in the frequency response with overshoot and ringing in the pulse response. Figure $7-49$ targets a $30^{\circ}$ phase margin for the OPA838. A $30^{\circ}$ phase margin produces a $5.7-\mathrm{dB}$ peaking in the frequency response at the amplifier output pin that is rolled off by the output RC pole; see Figure 8-7. This peaking can cause clipping for large signals driving a capacitive load. Increasing the R $\mathrm{R}_{\text {OUt }}$ value can reduce the peaking at the cost of a more band-limited overall response.


Figure 8-6. R Rout versus $C_{L}$ Test Circuit


Figure 8-7. Frequency Response to Output Pin and Capacitive Load

### 8.4 Device Functional Modes

### 8.4.1 Split-Supply Operation ( $\mathbf{1} .35 \mathrm{~V}$ to $\pm 2.7 \mathrm{~V}$ )

To facilitate testing with common lab equipment, the OPA838 EVM (see EVM board link) is built to allow splitsupply operation. This configuration eases lab testing because the midpoint between the power rails is ground, and most signal generators, network analyzers, oscilloscopes, spectrum analyzers, and other lab equipment have inputs and outputs with a ground reference. This simplifies characterization by removing the requirement for blocking capacitors.

Figure 8-8 shows a simple noninverting configuration analogous to Figure $8-1$ with a $\pm 2.5-\mathrm{V}$ supply and $\mathrm{V}_{\text {REF }}$ equal to ground. The input and output swing symmetrically around ground. For ease of use, split-supplies are preferred in systems where signals swing around ground. Using bipolar (or split) supplies shifts the thresholds for the shutdown control. The disable control is referenced from the negative supply, typically ground, in a single-supply application. However, to disable using a negative supply requires that the pin is set to within 0.55 V greater than the negative supply. If disable is not required, connect that pin to the positive supply to maintain correct operation, even for split-supply applications. Do not float the disable pin; assert the pin to a voltage.


Figure 8-8. Split-Supply Operation


Figure 8-9. Bipolar-Supply Step Response

### 8.4.2 Single-Supply Operation (2.7 V to 5.4 V )

Most newer systems use a single power supply to improve efficiency and to simplify power supply design. The OPA838 can be used with single-supply power (ground for the negative supply) with no change in performance from split supply, as long as the input and output pins are biased within the linear operating region of the device. The outputs nominally swing rail-to-rail with approximately a $100-\mathrm{mV}$ headroom required for linear operation. The inputs can swing below the negative rail (typically ground) and to within 1.3 V of the positive supply. For dc-coupled, single-supply operation, the higher-gain operating applications typical of a decompensated op amp keep the input swings less than the input swing limit to the positive supply. Typically, the $1.3-\mathrm{V}$ input headroom required to the positive supply does not limit operation.
Figure $8-10$ shows an example design that takes a $0-\mathrm{V}$ to $0.5-\mathrm{V}$ input range, level shifts the output up to 0.15 V for a $0-\mathrm{V}$ input using the $4.5-\mathrm{V}$ reference voltage common for $5-\mathrm{V}$ SAR ADCs, and sets the gain to produce a $4.1-\mathrm{V}$ output swing for the $0.5-\mathrm{V}$ input swing. This example assumes a $0-\Omega$ source that is required to sink the $39 \mu \mathrm{~A}$ required to bias the positive input pin to produce the $0.15-\mathrm{V}$ output for a $0-\mathrm{V}$ input. The $\mathrm{R}_{\mathrm{F}}$ and $\mathrm{R}_{\mathrm{G}}$ values
are scaled down slightly to provide bias current cancellation by matching the parallel combination of the two bias set-up resistors on the noninverting input. Figure 8-11 illustrates an example step response for this circuit that produces an output from 0.15 V for a $0-\mathrm{V}$ input to 4.35 V for a $0.5-\mathrm{V}$ input.


Figure 8-10. DC-Coupled, Single-Supply, Noninverting Interface With Output Level Shift


Figure 8-11. Unipolar Input to Level Shifted Output Step Response
If ac-coupling is acceptable, a simple way to operate single-supply is to run inverting. Figure $8-12$ shows a low-power, high-gain example. In this example, a gain of $-20 \mathrm{~V} / \mathrm{V}$ is implemented (inverting usually does not matter for ac-coupled channels) where the $\mathrm{V}+$ input is biased midscale. This example is showing an optional bias-current cancellation setup, which is not necessary unless the output dc level requires good accuracy. The parallel combination of the divider resistors plus the $80.7-\Omega$ isolating resistor match the feedback resistor value. With the blocking capacitor at the inverting input, the feedback resistor impedance must be matched to achieve bias current cancellation. In this $3-\mathrm{V}$ supply example, the two inputs and the output are biased at 1.5 V . This places the input pins in range and centers the output for maximum $\mathrm{V}_{\text {PP }}$ available. Figure 8-13 illustrates the small-signal response for this example showing a $\mathrm{f}_{-3 \mathrm{~dB}}$ range from a low-end cutoff of 887 Hz set by the input capacitor value to a $17.5-\mathrm{MHz}$ high-frequency cutoff.


Figure 8-12. Single-Supply Inverting Gain Stage With AC-Coupled Input


Figure 8-13. Inverting Single-Supply Response With AC-Coupled Input
These are only two of the many ways a single-supply design can be implemented. Many other methods exist, where using a dc reference voltage or ac-coupling are common. A good compilation of options can be found in Single-Supply Op Amp Design Techniques.

### 8.4.3 Power Shutdown Operation

As noted, the 6-pin packages that offer a power-shutdown feature must have that pin asserted. To retain the lowest possible shutdown power, no internal pullup resistors are present in the OPA838. The control threshold is referenced off the negative supply with a nominal internal threshold near 1 V greater than the negative supply. Worst-case tolerances dictate the required low-level voltage to provide a shutdown of 0.55 V (or less) greater than the negative supply, and 1.5 V (or more) greater than the negative supply to maintain enabled operation. The required control pin current is less than $\pm 50 \mathrm{nA}$. For SOT- $23-6$ applications that do not require a shutdown functionality, connect the disable control pin to the positive supply. For SC70 package applications that do not require a shutdown, use the 5 -pin package where the control pad is internally connected to the positive supply. When disabled, the output nominally goes to a high-impedance state. However, the feedback network provides a path for discharge for an off-state voltage condition. Figure 7-51 illustrates the turn-on time with a sinusoidal input that is relatively slow, while Figure 7-52 illustrates the turn-off time is fast. Figure 7-53 and Figure 7-54 illustrate the single-supply operation with a dc input to produce a midsupply output at gains of $6 \mathrm{~V} / \mathrm{V}$ and $10 \mathrm{~V} / \mathrm{V}$. In all cases, the output voltage transitions to a point close to the positive supply voltage and then moves to the desired output voltage $0.5 \mu \mathrm{~s}$ to $1.5 \mu \mathrm{~s}$ after the disable control line goes high. The supply current in shutdown is a low $0.1 \mu \mathrm{~A}$ nominally with a maximum $1 \mu \mathrm{~A}$.

## 9 Application and Implementation

## Note

Information in the following applications sections is not part of the TI component specification, and Tl does not warrant its accuracy or completeness. Tl's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 9.1 Application Information

### 9.1.1 Noninverting Amplifier

The OPA838 can be used as noninverting amplifier with signal input to the noninverting input $\left(\mathrm{V}_{\mathbb{I N}+}\right)$. Figure 8-1 illustrates a basic block diagram of the circuit. $V_{\text {REF }}$ is often ground when split supplies are used.

If $V_{I N}=V_{R E F}+V_{S I G}$, and the gain setting resistor $\left(R_{G}\right)$ is dc referenced to $V_{R E F}$, use Equation 1 to calculate the output of the amplifier.

$$
\begin{equation*}
V_{\mathrm{OUT}}=\mathrm{V}_{\mathrm{SIG}}\left(1+\frac{\mathrm{R}_{\mathrm{F}}}{\mathrm{R}_{\mathrm{G}}}\right)+\mathrm{V}_{\mathrm{REF}} \tag{1}
\end{equation*}
$$

The noninverting signal gain (also called the noise gain) of the circuit is set by:

$$
G=1+\frac{R_{F}}{R_{G}}
$$

$V_{\text {REF }}$ provides a reference around which the input and output signals swing. Output signals are in-phase with the input signals within the flat portion of the frequency response. For a high-speed, low-noise device like the OPA838, the values selected for $R_{F}$ (and the $R_{G}$ for the desired gain) can strongly influence the operation of the circuit. For the characteristic curves, the noninverting circuit of Figure $9-1$ shows the test configuration. Table 9-1 lists the recommended resistor values over gain.


Figure 9-1. Noninverting Characterization Circuit

Table 9-1 lists the recommended resistor values from target gains of $6 \mathrm{~V} / \mathrm{V}$ to $20 \mathrm{~V} / \mathrm{V}$. This table controls the $R_{F}$ and $R_{G}$ values to set the resistor noise contribution at approximately $40 \%$ of the total output noise power. This increases the spot noise at the output over what the op amp voltage noise produces by $20 \%$. Lower values reduce the output noise of any design at the cost of more power in the feedback circuit. Using the TINA model and simulation tool shows the impact of different resistor value choices on response shape and noise.

Table 9-1. Noninverting Recommended Resistor Values

| TARGET <br> AVERAGE | $\mathbf{R}_{\mathbf{F}}(\Omega)$ | $\mathbf{R}_{\mathbf{G}}(\Omega)$ | ACTUAL GAIN (V/V) | GAIN (dB) |
| :---: | :---: | :---: | :---: | :---: |
| 6 | 1000 | 200 | 6 | 15.56 |
| 7 | 1180 | 196 | 7.02 | 16.93 |
| 8 | 1370 | 196 | 7.99 | 18.05 |
| 9 | 1540 | 191 | 9.06 | 19.15 |
| 10 | 1690 | 187 | 10.04 | 20.03 |
| 11 | 1870 | 187 | 11 | 20.83 |
| 12 | 2050 | 187 | 11.96 | 21.56 |
| 13 | 2210 | 182 | 13.14 | 22.37 |
| 14 | 2370 | 182 | 14.02 | 22.94 |
| 15 | 2550 | 182 | 15.01 | 23.53 |
| 16 | 2870 | 178 | 16.05 | 24.11 |
| 17 | 3090 | 182 | 17.12 | 24.67 |
| 18 | 3240 | 178 | 17.98 | 25.09 |
| 19 | 3400 | 178 | 19.20 | 25.67 |
| 20 | 3570 | 20.1 | 26.06 |  |
| 21 |  |  | 21.06 | 26.47 |

### 9.1.2 Inverting Amplifier

The OPA838 can be used as an inverting amplifier with signal input to the inverting input ( $\mathrm{V}_{\text {IN-}}$ ) through the gain-setting resistor $\left(\mathrm{R}_{\mathrm{G}}.\right)$ Figure 8-2 illustrates a basic block diagram of the circuit.
If $V_{I N}=V_{\text {REF }}+V_{\text {SIG }}$, and the noninverting input is dc biased to $V_{\text {REF }}$, the output of the amplifier is calculated according to Equation 2:

$$
\begin{equation*}
v_{\text {OUT }}=V_{S I G}\left(\frac{-R_{F}}{R_{G}}\right)+V_{\text {REF }} \tag{2}
\end{equation*}
$$

The signal gain of the circuit $G=\frac{-R_{F}}{R_{G}}$ and $V_{R E F}$ provides a reference point around which the input and output signals swing. For bipolar-supply operation, $\mathrm{V}_{\text {REF }}$ is often GND. The output signal is $180^{\circ}$ out-of-phase with the input signal in the pass band of the application. Figure 9-2 illustrates the $50-\Omega$ input matched configuration used for the inverting characterization plots. In this case, an added termination resistor is placed in parallel with the input $R_{G}$ resistor to provide an impedance match to $50-\Omega$ test equipment. Table $9-2$ lists the suggested values for $\mathrm{R}_{\mathrm{F}}, \mathrm{R}_{\mathrm{G}}$, and $\mathrm{R}_{\mathrm{T}}$ for inverting gains from $-6 \mathrm{~V} / \mathrm{V}$ to $-20 \mathrm{~V} / \mathrm{V}$.


Figure 9-2. Inverting With Input Impedance Matching
Table 9-2. Inverting Recommended Resistor Values

| AVERAGE | $\mathrm{R}_{\mathrm{F}}(\mathbf{\Omega})$ | $\mathrm{R}_{\mathrm{G}}(\Omega)$ | EXACT $\mathrm{R}_{\text {T }}$ | STANDARD $\mathrm{R}_{\mathbf{T}}$ | INPUT $\mathrm{Z}_{1}$ | ACTUAL (V/V) | GAIN (dB) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| -6 | 1180 | 196 | 67.1 | 66.5 | 49.7 | -6.02 | 15.59 |
| -7 | 1370 | 196 | 67.1 | 66.5 | 49.7 | -6.99 | 16.89 |
| -8 | 1540 | 191 | 67.7 | 68.1 | 50.2 | -8.06 | 18.13 |
| -9 | 1690 | 187 | 68.2 | 68.1 | 49.9 | -9.04 | 19.12 |
| -10 | 1870 | 187 | 68.2 | 68.1 | 49.9 | -10 | 20 |
| -11 | 2050 | 187 | 68.2 | 68.1 | 49.9 | -10.96 | 20.80 |
| -12 | 2210 | 182 | 68.9 | 68.1 | 49.6 | -12.14 | 21.69 |
| -13 | 2370 | 182 | 68.9 | 68.1 | 49.6 | -13.02 | 22.29 |
| -14 | 2550 | 182 | 68.9 | 68.1 | 49.6 | -14.01 | 22.93 |
| -15 | 2740 | 182 | 68.9 | 68.1 | 49.6 | -15.05 | 23.55 |
| -16 | 2870 | 178 | 69.5 | 69.8 | 50.1 | -16.12 | 24.15 |
| -17 | 3090 | 182 | 68.9 | 69.8 | 50.5 | -16.98 | 24.6 |
| -18 | 3240 | 178 | 69.5 | 69.8 | 50.1 | -18.20 | 25.2 |
| -19 | 3400 | 178 | 69.5 | 69.8 | 50.1 | -19.10 | 25.62 |
| -20 | 3570 | 178 | 69.5 | 69.8 | 50.1 | -20.06 | 26.04 |

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### 9.1.3 Output DC Error Calculations

The OPA838 can provide excellent DC signal accuracy due to high open-loop gain, high common-mode rejection, high power-supply rejection, and low input offset voltage and bias current offset errors. To take full advantage of this low input offset voltage, pay careful attention to input bias current cancellation. The low-noise input stage for the OPA838 has a relatively high input bias current ( $1.6 \mu \mathrm{~A}$ typical out the pins) but with a close match between the two input currents. This is a negative rail input device using PNP input devices where the base current flows out of the device pins. A large resistor to ground on the $\mathrm{V}+$ input shifts positively because of the input bias current. The mismatch between the two input bias currents is very low, typically only $\pm 20 \mathrm{nA}$ of input offset current. Match the DC source impedances out of the two inputs to reduce the total output offset voltage. For example, one way to add bias current cancellation to the circuit in Figure $8-8$ is to insert a $165-\Omega$ series resistor into the noninverting input to match the parallel combination of $R_{F}$ and $R_{G}$ for this basic gain of $6 \mathrm{~V} / \mathrm{V}$ noninverting gain circuit. These same calculations apply to the output offset drift. Analyzing the simple circuit of Figure 8-8, the noise gain for the input offset voltage drift is $1+1 \mathrm{k} / 200=6 \mathrm{~V} / \mathrm{V}$. This results in an output drift term of $\pm 1.6 \mu \mathrm{~V} /{ }^{\circ} \mathrm{C} \times 6= \pm 9.6 \mu \mathrm{~V} /{ }^{\circ} \mathrm{C}$. Because the two impedances out of the inputs are matched, the residual error due to the maximum $\pm 500 \mathrm{pA} /{ }^{\circ} \mathrm{C}$ offset current drift is exactly that number times the $1-\mathrm{k} \Omega$ feedback resistor value, or $\pm 50 \mu \mathrm{~V} /{ }^{\circ} \mathrm{C}$. The total output DC error drift band is $\pm 59 \mu \mathrm{~V} /{ }^{\circ} \mathrm{C}$.

### 9.1.4 Output Noise Calculations

The decompensated voltage feedback of the OPA838 op amp offers among the lowest input voltage and current noise terms for any device with a supply current less than 1 mA . Figure $9-3$ shows the op amp noise analysis model that includes all noise terms. In this model, all the noise terms are shown as noise voltage or current density terms in $\mathrm{nV} / \sqrt{ } \mathrm{Hz}$ or $\mathrm{pA} / \sqrt{ } \mathrm{Hz}$.


Figure 9-3. Op-Amp Noise-Analysis Model
The total output spot noise voltage is computed as the square root of the squared contributing terms to the output noise voltage. This computation is adding all the contributing noise powers at the output by superposition, then taking the square root to return to a spot noise voltage. Equation 3 shows the general form for this output noise voltage using the terms presented in Figure 9-3.

$$
\begin{equation*}
\mathrm{E}_{\mathrm{O}}=\sqrt{\left[\mathrm{E}_{\mathrm{NI}}^{2}+\left(\mathrm{l}_{\mathrm{BN}} \mathrm{R}_{\mathrm{S}}\right)+4 k T R_{\mathrm{S}}\right] \mathrm{NG}^{2}+\left(\mathrm{l}_{\mathrm{BI}} \mathrm{R}_{\mathrm{F}}\right)^{2}+4 k T R_{\mathrm{F}} N G} \tag{3}
\end{equation*}
$$

Dividing this expression by the noise gain ( $N G=1+R_{F} / R_{G}$ ) gives the equivalent input-referred spot noise voltage at the noninverting input, as shown in Equation 4.

$$
\begin{equation*}
E_{N}=\sqrt{E_{N I}^{2}+\left(I_{B N} R_{S}\right)^{2}+4 k T R_{S}+\left(\frac{I_{B} R_{F}}{N G}\right)^{2}+\frac{4 k T R_{F}}{N G}} \tag{4}
\end{equation*}
$$

Using the resistor values shown in Table 9-1 with $R_{S}=0 \Omega$ results in a constant input-referred voltage noise of $2.86 \mathrm{nV} / \sqrt{ } \mathrm{Hz}$. Reducing the resistor values brings this number closer to the intrinsic $1.9 \mathrm{nV} / \sqrt{ } \mathrm{Hz}$ of the OPA838. Adding $R_{S}$ for bias current cancellation in noninverting mode adds the noise from $R_{S}$ to the total output noise; see Equation 3. In inverting mode, bypass the $R_{S}$ bias-current cancellation resistor with a capacitor for the best noise performance.

### 9.2 Typical Applications

### 9.2.1 High-Gain Differential I/O Designs

A high-gain differential-to-differential I/O circuit can be used to drive a second-stage FDA or a differential-to-single-ended stage. This circuit is frequently used in applications where high input impedance is required (for example, if the source cannot be loaded). Figure 9-3 illustrates an example design where the differential gain is $41 \mathrm{~V} / \mathrm{V}$. An added element between the two $\mathrm{R}_{\mathrm{G}}$ resistors increases the noise gain for the common-mode feedback. Make sure to provision for the added element; otherwise, a decompensated VFA (such as the OPA838) often oscillates. With only the $\mathrm{R}_{\mathrm{G}}$ elements in the differential I/O design, the common-mode feedback is unity-gain and often causes high-frequency, common-mode oscillations. To resolve this issue, split the $R_{G}$ elements in half and add a low-impedance path, such as a capacitor or a DC reference, between the two $R_{G}$ values.


Figure 9-4. High-Gain Differential I/O Stage
Integrated results are available, but the OPA838 provides a low-power, high-frequency result. For best CMRR performance, match the resistors. A good rule is CMRR is approximately equal to the resistor tolerance; therefore, a $0.1 \%$ tolerance provides approximately $60-\mathrm{dB}$ CMRR.

## 92-1.1 Design Requirements

As an example design, start with the circuit in Figure 9-4.

- Set the target gain and split the $\mathrm{R}_{\mathrm{G}}$ element in half. For this example, target a gain of $41 \mathrm{~V} / \mathrm{V}$.
- Assess the DC common-mode biasing on the noninverting inputs. The DC biasing must be in range and have a gain of 1 to the output. This is not illustrated in Figure 9-3.
- If a DC reference is used as the mid- $\mathrm{R}_{\mathrm{G}}$ bias, setting the reference equal to the noninverting input bias voltage sets the output common-mode to that voltage. Using a capacitor as illustrated in Figure 9-3 accomplishes the same results.

OPA838

### 9.2.1.2 Detailed Design Procedure

- Set the total $R_{G}$ value near the high gain values using Table $9-1$. This $178-\Omega$ total must be split for a center tap to increase the common-mode noise gain, as shown by the 88.7- $\Omega$ value in Figure 9-4.
- Set $R_{F}$ using a standard value near the calculated from solving Equation 1 using half of the total $R_{G}$ value.
- Simulate the common-mode noise with different elements on the $R_{G}$ center tap as shown in Figure 9-5.

Decide which is most appropriate to the application.
The common-mode loop instability without the $R_{G}$ center tap is not often apparent in the closed-loop differential simulations. The common-mode loop instability without the $R_{G}$ center tap can often be detected in a commonmode output-noise simulation as Figure 9-5 shows. Grounding the inputs Figure 9-4 and running an output-noise simulation for the common-mode tap point in Figure 9-3 shows a peaking in the noise at high frequency. This peaking indicates low-phase margin for the common-mode loop. Figure 9-5 shows this peaking in the lowest noise curve, with two options for improving phase margin. The first option used in Figure 9-4 is a capacitor to ground set to increase the common-mode noise gain only at higher frequencies. This increase can be seen by the peaking in the common-mode noise of Figure 9-5. Another alternative is to provide a dc voltage reference on the $\mathrm{R}_{\mathrm{G}}$ center tap. This method raises the common-mode noise gain from dc and beyond. Neither of these latter two options show any evidence of low phase-margin peaking. These two options do increase the output common-mode noise significantly at lower frequencies. Typically, an increase in output common-mode noise is more acceptable than low-phase margin because the next stage (FDA, ADC, differential to single stage) rejects common-mode noise.

Using the $10-\mathrm{nF}$ center tap capacitor, Figure $9-6$ shows the differential I/O small-signal response showing the expected $300 \mathrm{MHz} / 41 \approx 7.3 \mathrm{MHz}$ closed-loop bandwidth. The capacitor to ground between the $\mathrm{R}_{\mathrm{G}}$ elements does not impact the differential frequency response.

### 9.2.1.3 Application Curves



### 9.2.2 Transimpedance Amplifier

A common application for a high-gain-bandwidth voltage-feedback op amp is to amplify a small photodiode current from a capacitive detector. Figure 9-7 shows the front-page transimpedance circuit with more detail. Here, a fixed -0.23 negative voltage generator (LM7705) is used on the negative supply to make sure the output has adequate headroom when the output is at 0 V . The transimpedance stage is designed here for a $2.4-\mathrm{MHz}$ flat (Butterworth) response while a simple RC post-filter band-limits the broadband noise and sets the overall bandwidth to 1 MHz . The requirements for a high-dynamic-range transimpedance (or charge) amplifier include the very low input voltage noise intrinsic to a decompensated device like the OPA838. The noise gain over frequency for this type of circuit starts out at unity gain, and then begins to peak with a single zero response. This peaking is due to the pole formed in the feedback by the feedback resistor and the total capacitance on the inverting input. That noise gain response is flattened out at higher frequencies by the feedback capacitor value to be the $1+C_{S} / C_{F}$ capacitor ratio. This noise gain is normally a very high, allowing the decompensated OPA838 to be applied to this application. The noise gain is intentionally peaked to a high value in this application; therefore, the very low input voltage noise ( $1.8 \mathrm{nV} / \mathrm{VHz}$ ) of the OPA838 improves dynamic range.


Figure 9-7. 100-k $\Omega$ Wide Bandwidth Transimpedance Design

### 9.2.2.1 Design Requirements

To implement a controlled frequency response transimpedance design, set the transimpedance stage amplifier bandwidth higher than a controlled post RC filter. This allows variation in the source capacitance and amplifier gain bandwidth product with less overall bandwidth variation to the final output. In this example design:

- Assume a nominal source capacitance value of 100 pF . This normally comes from the capacitance versus reverse bias plot for the photodiode. No reverse bias is illustrated in Figure 9-8, but the current source is typically a back biased diode with a negative supply on the anode and the cathode connected to the op amp inverting input. In this polarity, the signal current sinks into the diode and raises the op amp output voltage above ground.
- For the best dc precision, add a matching resistor on the noninverting input to reduce the input bias current error to $\mathrm{l}_{\mathrm{OS}} \times \mathrm{R}_{\mathrm{F}}$. This resistor adds to the input voltage noise; TI recommends bypassing that resistor with as large as a capacitor as required to roll off resistor noise. This capacitor has a relatively low frequency self resonance that interacts with the input stage and can impair stability. Add a small series $20-\Omega$ resistor from the capacitor into the noninverting input to de-Q the resonant source impedance without adding too much noise.
- Set the feedback capacitor to achieve the desired frequency response shape.
- Add a post RC filter to control the overall bandwidth to 1 MHz . In this example, a $2.2-\mathrm{nF}$ capacitor allows a low $73.2-\Omega$ series resistor. When driving a sampling ADC (like a SAR), this combination helps reduce the sampling glitch and speed settling time.

OPA838

### 9.2.2.2 Detailed Design Procedure

The primary design requirement is to set the achievable transimpedance gain and compensate the operational amplifier with $C_{F}$ for the desired response shape. A detailed transimpedance design methodology is available in Transimpedance Considerations for High-Speed Amplifiers. With a source capacitance set and the amplifier selected to provide a particular gain bandwidth product, the achievable transimpedance gain and resulting Butterworth bandwidth are tightly coupled as Equation 5 illustrates. Use Equation 6 to solve for a maximum $R_{F}$ value. When the $R_{F}$ is selected, the feedback pole is set by Equation 7 to be at 0.707 of the characteristic frequency. At that compensation point, the closed-loop bandwidth is that characteristic frequency with a Butterworth response.

- With the $100-\mathrm{pF}$ source capacitance, $300-\mathrm{MHz}$ gain bandwidth product, and the $2.2-\mathrm{MHz}$ closed-loop bandwidth target in the transimpedance stage, solve Equation 6 for a maximum gain of $100 \mathrm{k} \Omega$.
- Set the feedback pole at 0.707 times that $2.2-\mathrm{MHz}$ Butterworth bandwidth. This sets the target $1 /\left(2 \pi \times R_{F} \times\right.$ $\left.\mathrm{C}_{\mathrm{F}}\right)=1.55 \mathrm{MHz}$. Solving for $\mathrm{C}_{\mathrm{F}}$ sets the target to 1 pF
- If dc precision is desired, add a $100-\mathrm{k} \Omega$ resistor to ground on the noninverting input. If DC precision is not required, ground the noninverting input
- Add a resistor noise filtering capacitor in parallel with the $100-\mathrm{k} \Omega$ resistor.
- Add a small series resistor isolating this capacitor from the noninverting input.
- Select a final filter capacitor for the load. (In this example, a value of 2.2 nF is used as a typical SAR input capacitor.)
- Add a series resistor to the final filter capacitor to form a 1-MHz pole. In this example, that is $73.2 \Omega$.
- Confirm this resistor is greater than the minimum recommended value illustrated in Figure 7-49.

$$
\begin{equation*}
\mathrm{F}_{-3 \mathrm{~dB}} \approx \sqrt{\frac{\mathrm{GBP}}{2 \pi \mathrm{R}_{f} \mathrm{C}_{\mathrm{S}}}} \tag{5}
\end{equation*}
$$

$\mathrm{R}_{f \max } \approx \frac{\mathrm{GBP}}{\mathrm{F}_{-3 \mathrm{~dB}}^{2} 2 \pi \mathrm{C}_{\mathrm{S}}}$

$$
\begin{equation*}
\frac{1}{2 \pi \mathrm{R}_{f} \mathrm{C}_{f}}=0.707 \times \sqrt{\frac{\mathrm{GBP}}{2 \pi \mathrm{R}_{f} \mathrm{C}_{S}}} \tag{6}
\end{equation*}
$$

Implementing this design and simulating the performance using the TINA model for the response to the output pin and to the final capacitive load shows the expected results of Figure $9-8$. Here, the exact $2.2-\mathrm{MHz}$ flat Butterworth response to the output pin is shown with the final single pole rolloff at 1 MHz at the final $2.2-\mathrm{nF}$ capacitor.

### 9.2.2.3 Application Curve



Figure 9-8. Small-Signal Response for 100-k $\mathbf{\Omega}$ Transimpedance Gain

### 9.3 Power Supply Recommendations

The OPA838 device is intended to work in a supply range of 2.7 V to 5.4 V . Good power-supply bypassing is required. Minimize the distance (less than 0.1 inch) from the power-supply pins to high-frequency, $0.1-\mu \mathrm{F}$ decoupling capacitors. A larger capacitor ( $2.2 \mu \mathrm{~F}$ is typical) is used with a high-frequency, $0.1-\mu \mathrm{F}$ supplydecoupling capacitor at the device supply pins. For single-supply operation, only the positive supply has these capacitors. When a split-supply is used, use these capacitors for each supply to ground. If necessary, place the larger capacitors further from the device and share these capacitors among several devices in the same area of the PCB. Avoid narrow power and ground traces to minimize inductance between the pins and the decoupling capacitors. An optional $0.1-\mu \mathrm{F}$ supply decoupling capacitor across the two power supplies (for bipolar operation) reduces second harmonic distortion.
The OPA838 has a positive supply current temperature coefficient; see Figure 7-57. This helps improve the input offset voltage drift. Supply current requirements in system design must account for this effect using the maximum intended ambient and Figure $7-57$ to size the supply required. The very low power dissipation for the OPA838 typically does not require any special thermal design considerations. For the extreme case of $125^{\circ} \mathrm{C}$ operating ambient, use the approximate maximum $200^{\circ} \mathrm{C} / \mathrm{W}$ for the three packages, and a maximum internal power of
$5.4-\mathrm{V}$ supply $\times 1.25-\mathrm{mA} 125^{\circ} \mathrm{C}$ supply current from Figure $7-57$ gives a maximum internal power of 6.75 mW . This only gives a $1.35^{\circ} \mathrm{C}$ rise from ambient to junction temperature which is well below the maximum $150^{\circ} \mathrm{C}$ junction temperature. Load power adds to this, but also increases the junction temperature only slightly over ambient temperature.

### 9.4 Layout

### 9.4.1 Layout Guidelines

The OPA838 EVM can be used as a reference when designing the circuit board. TI recommends following the EVM layout of the external components near to the amplifier, ground plane construction, and power routing as closely as possible. General guidelines are listed below:

1. Signal routing must be direct and as short as possible into and out of the op amp.
2. The feedback path must be short and direct avoiding vias if possible.
3. Ground or power planes must be removed from directly under the negative input and output pins of the amplifier.
4. TI recommends placing a series output resistor as close to the output pin as possible when driving capacitive or matched loads.
5. A $2.2-\mu \mathrm{F}$ power-supply decoupling capacitor must be placed within two inches of the device and can be shared with other op amps. For split-supply operation, a capacitor is required for both supplies.
6. A $0.1-\mu \mathrm{F}$ power-supply decoupling capacitor must be placed as close to the supply pins as possible, preferably within 0.1 inch. For split-supply operation, a capacitor is required for both supplies.
7. The $\overline{\mathrm{PD}}$ pin uses logic levels referenced off the negative supply. If the pin is not used, the pin must tie to the positive supply to enable the amplifier. If the pin is used, the pin must be actively driven. A bypass capacitor is not necessary, but is used for EMI rejection in noisy environments.

### 9.4.2 Layout Example



Figure 9-9. EVM Layout Example

## 10 Device and Documentation Support

### 10.1 Device Support

### 10.1.1 TINA-TI ${ }^{\text {TM }}$ Simulation Model Features

The TINA-TI ${ }^{\text {TM }}$ simulation software device model is available on the product folder www.ti.com in a typical application circuit file. The model includes numerous features intended to speed designer progress over a wide range of application requirements. The following list shows the performance parameters included in the model:

- For the small-signal response shape with any external circuit:
- Differential open-loop gain and phase
- Parasitic input capacitance
- Open-loop differential output impedance
- For noise simulations:
- Input differential spot voltage noise and a $100-\mathrm{Hz} 1 / \mathrm{f}$ corner
- Input current noise on each input with a $6-\mathrm{kHz} 1 / \mathrm{f}$ corner
- For time-domain, step-response simulations:
- Differential slew rate
- I/O headroom models to predict clipping
- Input stage diodes to predict overdrive limiting
- Fine-scale, dc precision terms:
- PSRR
- CMRR
- Nominal input offset voltage
- Nominal input offset current
- Nominal input bias current

The Typical Characteristics table provides more detail than the macromodels can provide. Some of the unmodeled features include:

- Harmonic distortion
- Temperature drift in dc error ( $\mathrm{V}_{\mathrm{IO}}$ and $\mathrm{I}_{\mathrm{OS}}$ )
- Overdrive recovery time
- Turn-on and turn-off times using the power-down feature


### 10.2 Documentation Support

### 10.2.1 Related Documentation

For related documentation see the following:
Texas Instruments, OPA835DBV, OPA836DBV EVM user's guide

### 10.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on Subscribe to updates to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 10.4 Support Resources

TI E2E ${ }^{\text {TM }}$ support forums are an engineer's go-to source for fast, verified answers and design help - straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

### 10.5 Trademarks

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### 10.6 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.
ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 10.7 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

## Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

INSTRUMENTS

## PACKAGING INFORMATION

| Orderable Device | Status <br> (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan <br> (2) | Lead finish/ Ball material <br> (6) | MSL Peak Temp <br> (3) | Op Temp ( ${ }^{\circ} \mathrm{C}$ ) | Device Marking <br> (4/5) | Samples |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OPA838IDBVR | ACTIVE | SOT-23 | DBV | 6 | 3000 | RoHS \& Green | NIPDAU | Level-2-260C-1 YEAR | -40 to 125 | 1C3F | Samples |
| OPA838IDBVT | ACTIVE | SOT-23 | DBV | 6 | 250 | RoHS \& Green | NIPDAU | Level-2-260C-1 YEAR | -40 to 125 | 1C3F | Samples |
| OPA838IDCKR | ACTIVE | SC70 | DCK | 5 | 3000 | RoHS \& Green | NIPDAU | Level-2-260C-1 YEAR | -40 to 125 | 17Q | Samples |
| OPA838IDCKT | ACTIVE | SC70 | DCK | 5 | 250 | RoHS \& Green | NIPDAU | Level-2-260C-1 YEAR | -40 to 125 | 17Q | Samples |
| OPA838SIDCKR | ACTIVE | SC70 | DCK | 6 | 3000 | RoHS \& Green | NIPDAU | Level-2-260C-1 YEAR | -40 to 125 | 19C | Samples |
| OPA838SIDCKT | ACTIVE | SC70 | DCK | 6 | 250 | RoHS \& Green | NIPDAU | Level-2-260C-1 YEAR | -40 to 125 | 19C | Samples |

${ }^{(1)}$ The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device
${ }^{(2)}$ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed $0.1 \%$ by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free"
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption
Green: TI defines "Green" to mean the content of Chlorine ( Cl ) and Bromine ( Br ) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement
${ }^{(3)}$ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
${ }^{(4)}$ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
${ }^{(5)}$ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
${ }^{(6)}$ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION



TAPE DIMENSIONS


| A0 | Dimension designed to accommodate the component width |
| :--- | :--- |
| B0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

*All dimensions are nominal

| Device | Package <br> Type | Package <br> Drawing | Pins | SPQ | Reel <br> (iameter <br> $(\mathbf{m m})$ | Reel <br> Width <br> W1 (mm) | A0 <br> $(\mathbf{m m})$ | B0 <br> $(\mathbf{m m})$ | K0 <br> $(\mathbf{m m})$ | P1 <br> $(\mathbf{m m})$ | W <br> $(\mathbf{m m})$ | Pin1 <br> Quadrant |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OPA838IDBVR | SOT-23 | DBV | 6 | 3000 | 178.0 | 9.0 | 3.23 | 3.17 | 1.37 | 4.0 | 8.0 | Q3 |
| OPA838IDBVT | SOT-23 | DBV | 6 | 250 | 178.0 | 9.0 | 3.23 | 3.17 | 1.37 | 4.0 | 8.0 | Q3 |
| OPA838IDCKR | SC70 | DCK | 5 | 3000 | 178.0 | 9.0 | 2.4 | 2.5 | 1.2 | 4.0 | 8.0 | Q3 |
| OPA838IDCKT | SC70 | DCK | 5 | 250 | 178.0 | 9.0 | 2.4 | 2.5 | 1.2 | 4.0 | 8.0 | Q3 |
| OPA838SIDCKR | SC70 | DCK | 6 | 3000 | 178.0 | 9.0 | 2.4 | 2.5 | 1.2 | 4.0 | 8.0 | Q3 |
| OPA838SIDCKT | SC70 | DCK | 6 | 250 | 178.0 | 9.0 | 2.4 | 2.5 | 1.2 | 4.0 | 8.0 | Q3 |


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OPA838IDBVR | SOT-23 | DBV | 6 | 3000 | 180.0 | 180.0 | 18.0 |
| OPA838IDBVT | SOT-23 | DBV | 6 | 250 | 180.0 | 180.0 | 18.0 |
| OPA838IDCKR | SC70 | DCK | 5 | 3000 | 180.0 | 180.0 | 18.0 |
| OPA838IDCKT | SC70 | DCK | 5 | 250 | 180.0 | 180.0 | 18.0 |
| OPA838SIDCKR | SC70 | DCK | 6 | 3000 | 180.0 | 180.0 | 18.0 |
| OPA838SIDCKT | SC70 | DCK | 6 | 250 | 180.0 | 180.0 | 18.0 |



ALTERNATIVE PACKAGE SINGULATION VIEW

## NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.
4. Leads $1,2,3$ may be wider than leads $4,5,6$ for package orientation.
5. Refernce JEDEC MO-178.


SOLDER MASK DETAILS

NOTES: (continued)
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

NOTES: (continued)
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



ALTERNATIVE PACKAGE SINGULATION VIEW

## NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side


NOTES: (continued)
7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.


SOLDER PASTE EXAMPLE BASED ON 0.125 THICK STENCIL SCALE:18X

NOTES: (continued)
9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.


ALTERNATIVE PACKAGE SINGULATION VIEW

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
4. Falls within JEDEC MO-203 variation AB.


NOTES: (continued)
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.


SOLDER PASTE EXAMPLE BASED ON 0.125 THICK STENCIL

SCALE:18X

NOTES: (continued)
7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

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